CBRHD-01

HIGH DENSITY
0.8 AMP DUAL IN LINE
BRIDGE RECTIFIER

HD DIP CASE

- This series is UL listed: file number E130224

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHD-01 is a silicon full wave bridge rectifier mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

MARKING CODE: CBD1

FEATURES:

- Efficient use of board space: requires only 42mm^2 of board space vs. 120mm^2 of board space needed for industry standard 1.0 Amp surface mount bridge rectifier.
- 50% higher density (Amps/mm^2) than the industry standard 1.0 Amp surface mount bridge rectifier.
- Glass passivated chips for high reliability.

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
DC Blocking Voltage	V_R	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average Forward Current (T_A=40°C) (Note1)	I_O	0.5	A
Average Forward Current (T_A=40°C) (Note 2)	I_O	0.8	A
Peak Forward Surge Current	I_{FSM}	30	A
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance (Note 3)	Θ_{JA}	85	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	V_R= 100V		5.0	μA
I_R	V_R= 100V, T_A=125°C		500	μA
V_F	I_F=400mA		1.0	V
C_J	V_R=4.0V, f=1.0MHz	9.0		pF

Notes: (1) Mounted on Glass-Epoxy PCB.
(2) Mounted on Ceramic PCB.
(3) Mounted on PCB with 0.5” x 0.5” copper pads.

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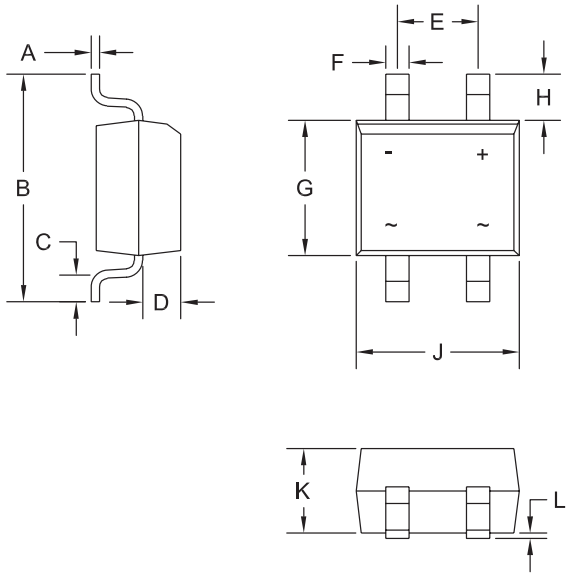
HD DIP CASE - MECHANICAL OUTLINE



R2

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.275	-	7.00
C	0.027	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.090	0.106	2.30	2.70
F	0.019	0.031	0.50	0.80
G	0.150	0.165	3.80	4.20
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.090	0.106	2.30	2.70
L	0.000	0.008	0.00	0.20

HD DIP (REV: R2)

MARKING CODE: CBD1

R1 (19-October 2007)